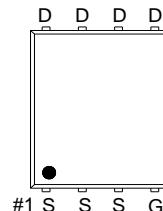
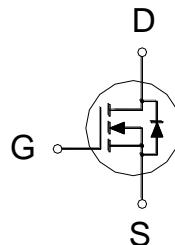


NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK600BA
PDFN 5x6P
Halogen-Free & Lead-Free****PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	9.5mΩ	40A



G. GATE
D. DRAIN
S. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ³	$T_C = 25^\circ\text{C}$	I_D	40	A
	$T_C = 100^\circ\text{C}$		25	
Pulsed Drain Current ¹		I_{DM}	100	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	10.7	W
	$T_A = 70^\circ\text{C}$		8.6	
Avalanche Current		I_{AS}	18	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	16.2	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	27.8	W
	$T_C = 100^\circ\text{C}$		11	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2	W
	$T_A = 70^\circ\text{C}$		1.3	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		63	°C / W
Junction-to-Case	$R_{\theta JC}$		4.5	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

³Package limitation current is 20A.

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**N-Channel Enhancement Mode
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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 24\text{V}, V_{\text{GS}} = 0\text{V}$			1	
		$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			10	μA
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 9\text{A}$		9.7	13.5	
		$V_{\text{GS}} = 10\text{V}, I_D = 9.5\text{A}$		7.4	9.5	$\text{m}\Omega$
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 9.5\text{A}$		62		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$	486	608	729	pF
Output Capacitance	C_{oss}		89	112	134	
Reverse Transfer Capacitance	C_{rss}		44	74	104	
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$	1.4	2.8	42	Ω
Total Gate Charge ²	Q_g	$V_{\text{GS}} = 10\text{V}$	11	14	17	nC
			5.8	7.3	8.8	
Gate-Source Charge ²	Q_{gs}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 9.5\text{A}$	1.6	2	2.4	nC
Gate-Drain Charge ²	Q_{gd}		2.2	3.7	5.2	
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$	$V_{\text{DS}} = 15\text{V}, I_D \geq 9.5\text{A}, V_{\text{GS}} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		13		nS
Rise Time ²	t_r			37		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$			48		
Fall Time ²	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current ³	I_S	$I_F = 9.5\text{A}, V_{\text{GS}} = 0\text{V}$			25	A
Forward Voltage ¹	V_{SD}				1.1	V
Reverse Recovery Time	t_{rr}		5.9	11.7	18	nS
Reverse Recovery Charge	Q_{rr}		1.5	3	4.5	nC

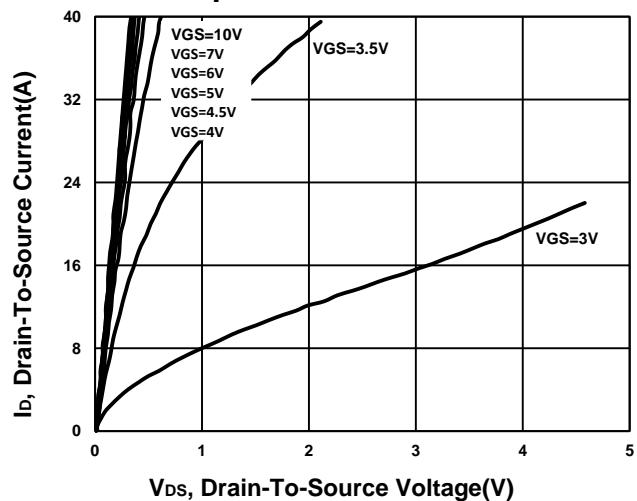
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Package limitation current is 20A.

NIKO-SEM

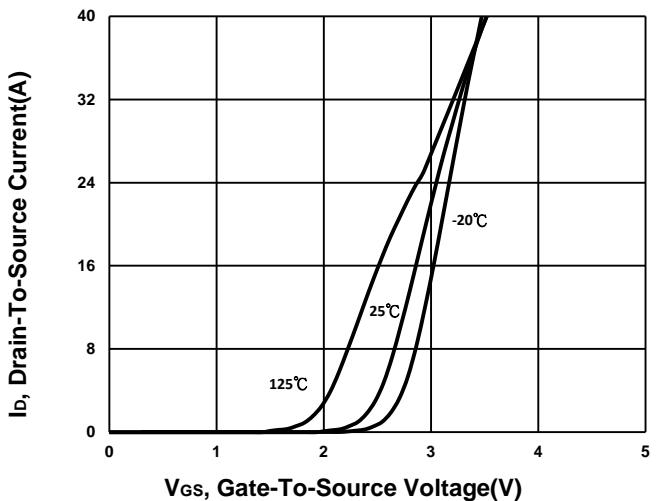
**N-Channel Enhancement Mode
Field Effect Transistor**

**PK600BA
PDFN 5x6P
Halogen-Free & Lead-Free**

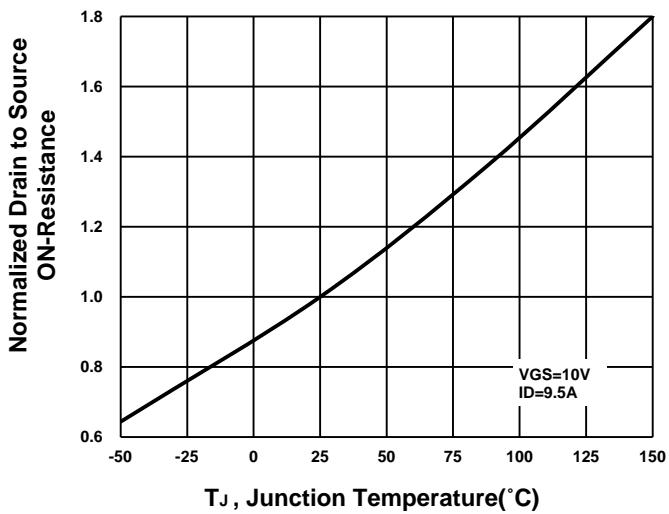
Output Characteristics



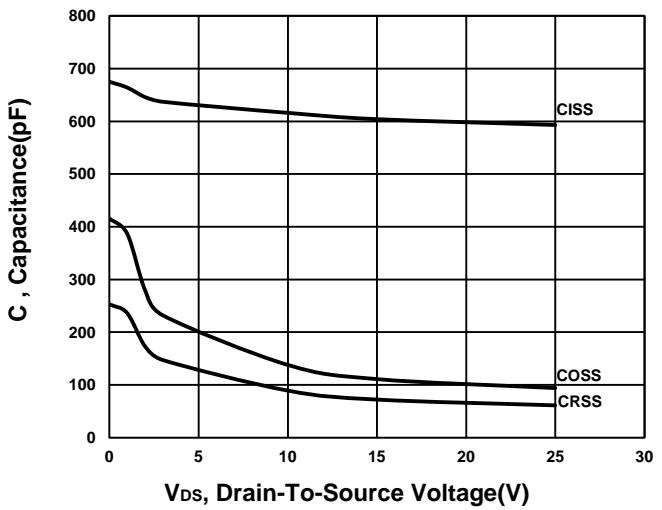
Transfer Characteristics



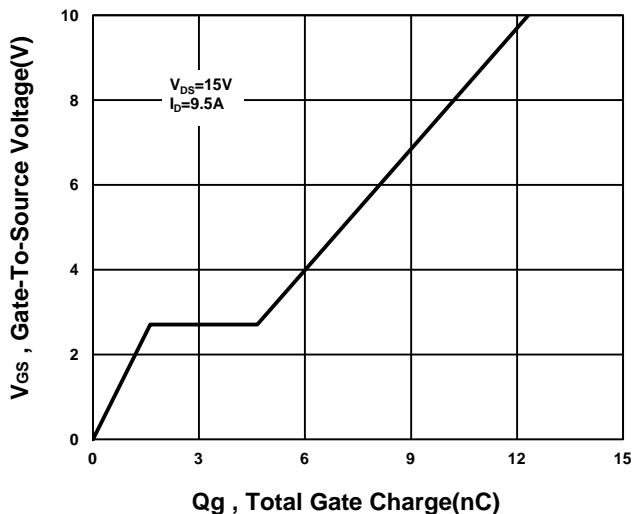
On-Resistance VS Temperature



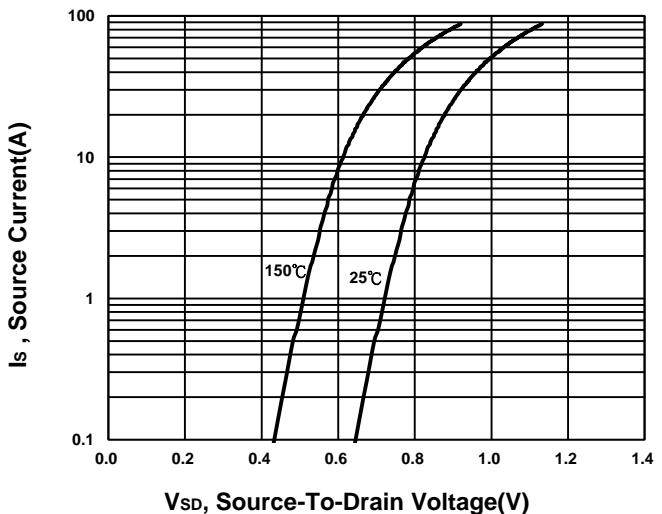
Capacitance Characteristic



Gate charge Characteristics



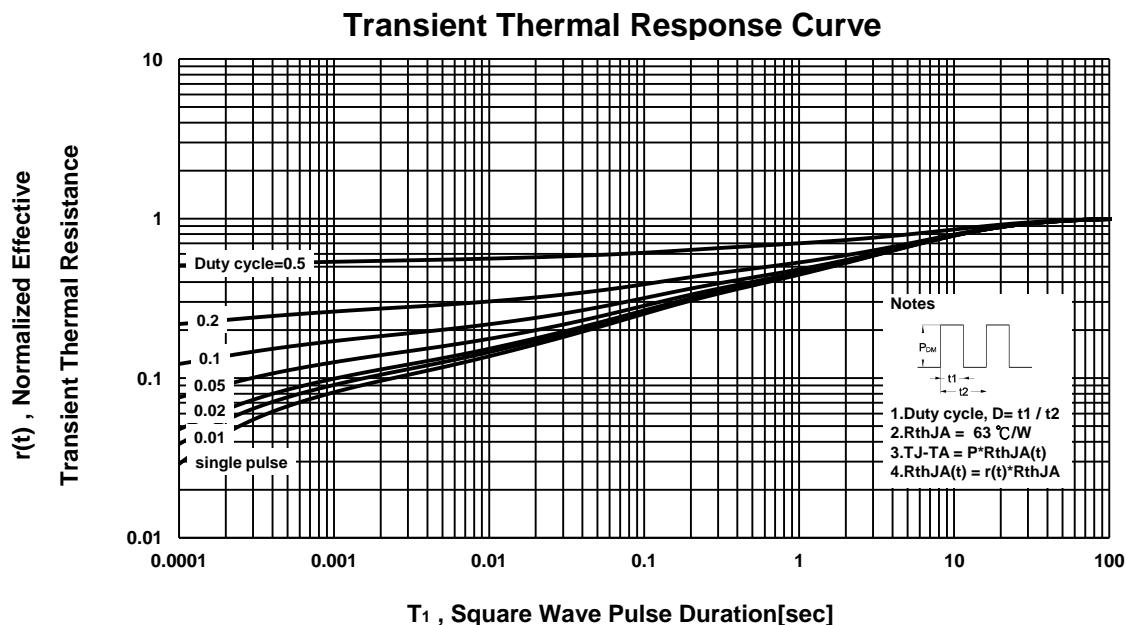
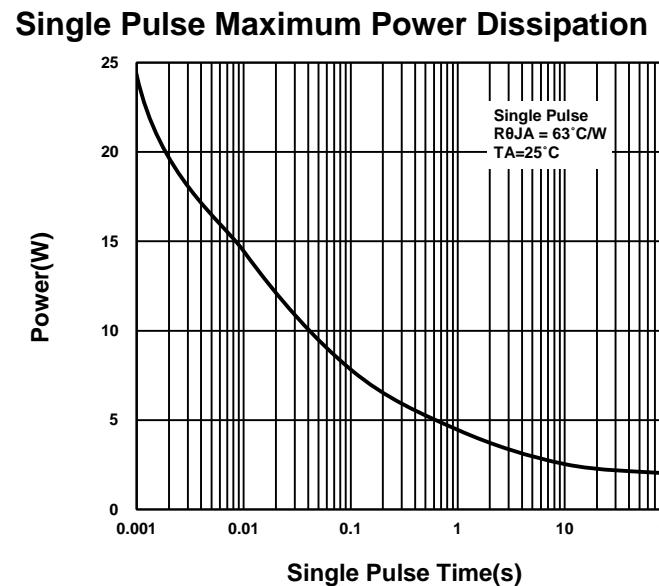
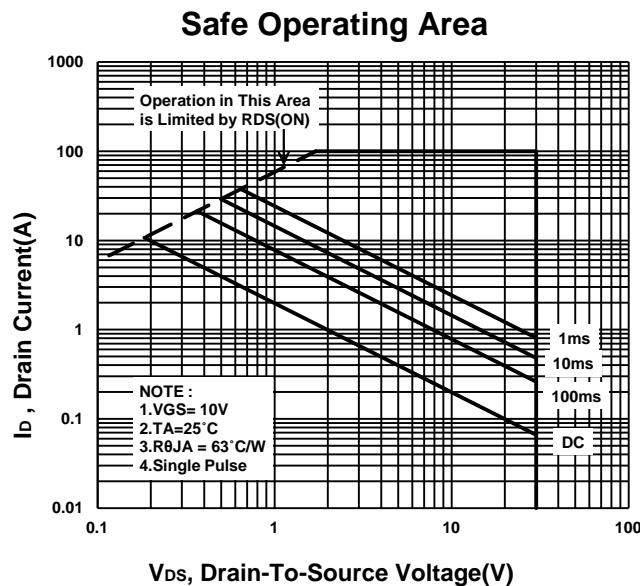
Source-Drain Diode Forward Voltage



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